

MOSFETs Silicon N-channel MOS (U-MOSⅧ)

# TPN4R203NC

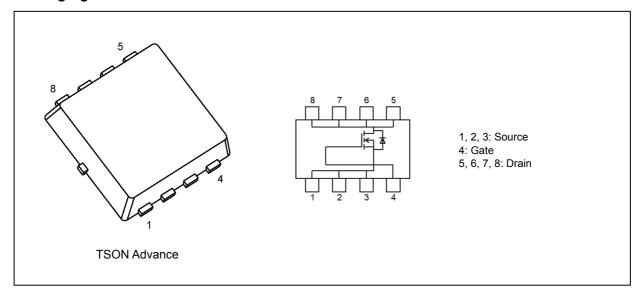
## 1. Applications

- · Lithium-Ion Secondary Batteries
- · Power Management Switches

#### 2. Features

- (1) Small, thin package
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 3.5 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (3) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- (4) Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 0.2 mA)

## 3. Packaging and Internal Circuit



1

Start of commercial production



# 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characterist	ics		Symbol	Rating	Unit
Drain-source voltage			$V_{DSS}$	30	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I <sub>D</sub>	53	Α
Drain current (DC)		(Note 1)	I <sub>D</sub>	23	
Drain current (pulsed)	(1 ms)	(Note 1)	I <sub>DP</sub>	146	
Power dissipation	(T <sub>c</sub> = 25°C)		$P_{D}$	22	W
Power dissipation	(t = 10 s)	(Note 3)	$P_D$	1.9	
Power dissipation	(t = 10 s)	(Note 4)	$P_{D}$	0.7	
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	62	mJ
Avalanche current			I <sub>AR</sub>	23	Α
Channel temperature			T <sub>ch</sub>	150	ů
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characterist	tics		Symbol	Max	Unit
Channel-to-case thermal resistance	$(T_c = 25^{\circ}C)$		R <sub>th(ch-c)</sub>	5.68	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R <sub>th(ch-a)</sub>	65.7	
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R <sub>th(ch-a)</sub>	178	

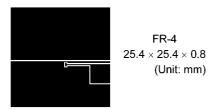
Note 1: Ensure that the channel temperature does not exceed 150°C.

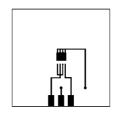
Note 2: Limited by silicon chip capability. Package limit is 45 A.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5:  $V_{DD}$  = 24 V,  $T_{ch}$  = 25°C (initial), L = 0.091 mH,  $I_{AR}$  = 23 A





FR-4  $25.4 \times 25.4 \times 0.8$  (Unit: mm)

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

# 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μΑ
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30			V
Drain-source breakdown voltage (Note 6)	V <sub>(BR)DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15			
Gate threshold voltage	$V_{th}$	$V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ mA}$	1.3	_	2.3	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 11.5 A	_	5.1	6.4	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 11.5 A	_	3.5	4.2	

Note 6: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

# 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	1370	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	110	_	
Output capacitance	C <sub>oss</sub>		_	420	_	
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	_	5.0	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	13	_	
Switching time (fall time)	t <sub>f</sub>		_	14	_	
Switching time (turn-off time)	t <sub>off</sub>		ı	52	_	

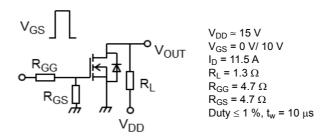


Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 23 \text{ A}$	_	24	_	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	5	_	
Gate-drain charge	$Q_{gd}$		_	4.9	_	

## 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

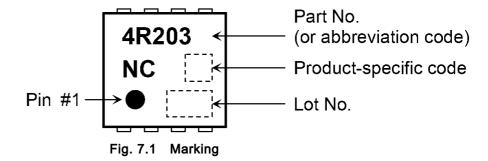
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 7)	I <sub>DRP</sub>	_	_		146	Α
Diode forward voltage		$V_{DSF}$	I <sub>DR</sub> = 23 A, V <sub>GS</sub> = 0 V			-1.2	V

Note 7: Ensure that the channel temperature does not exceed 150°C.

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# 7. Marking





#### 8. Characteristics Curves (Note)

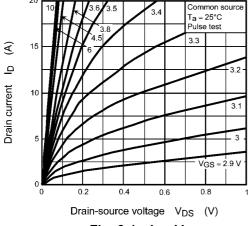
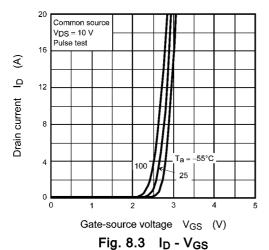


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>



Pulse test

100

Output

Outpu

Common source

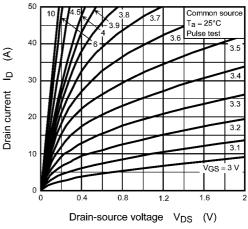


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

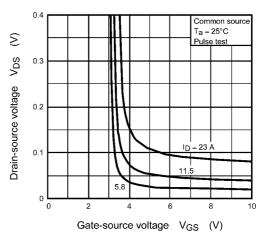


Fig. 8.4 VDS - VGS

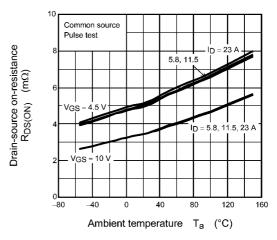


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub>



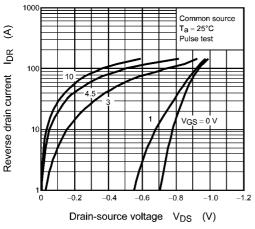


Fig. 8.7 IDR - VDS

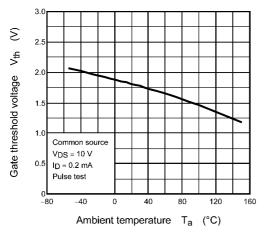
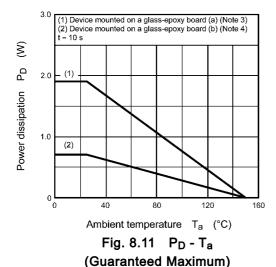


Fig. 8.9 V<sub>th</sub> - T<sub>a</sub>



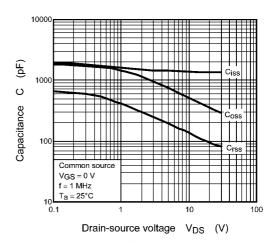


Fig. 8.8 Capacitance - V<sub>DS</sub>

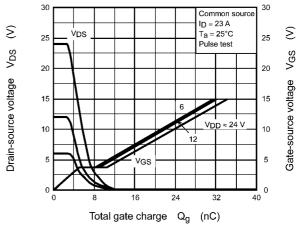
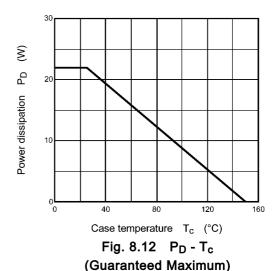


Fig. 8.10 Dynamic Input/Output Characteristics



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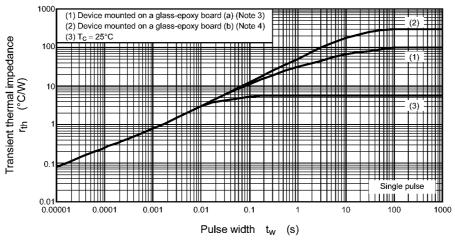


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

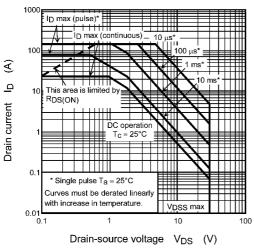


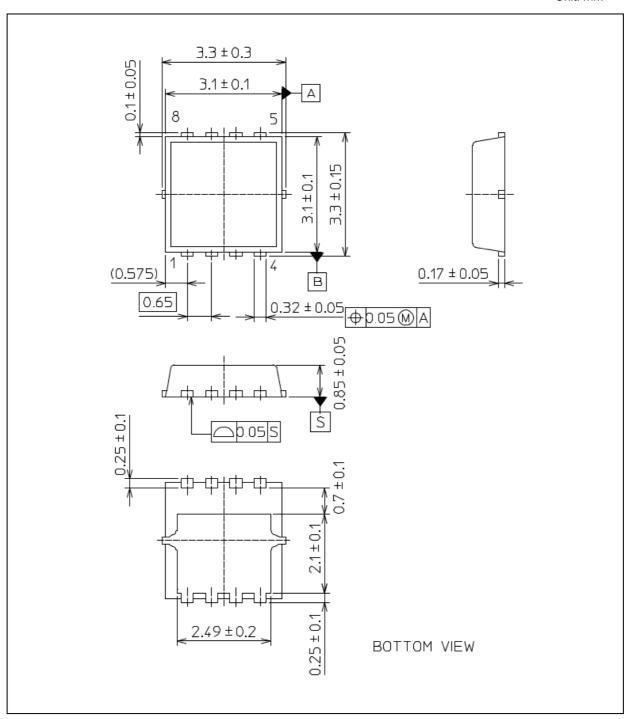
Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



Weight: 0.026 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance

Rev.5.0



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